

# ZXTN25050DFH

## 50V, SOT23, NPN medium power transistor

### Summary

$BV_{CEX} > 150V$

$BV_{CEO} > 50V$

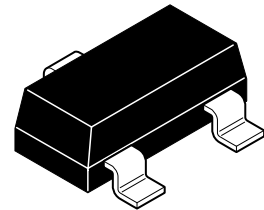
$BV_{ECO} > 5V$

$I_{C(cont)} = 4A$

$V_{CE(sat)} < 60mV @ 1A$

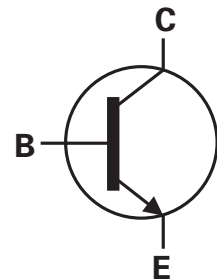
$R_{CE(sat)} = 40m\Omega$

$P_D = 1.25W$



### Description

Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.

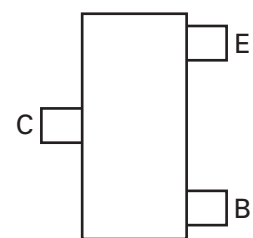


### Features

- High power dissipation SOT23 package
- High peak current
- High gain
- Low saturation voltage
- 150V forward blocking voltage
- 5V reverse blocking voltage

### Applications

- MOSFET gate drivers
- Power switches
- Motor control
- DC fans
- DC-DC converters



Pinout - top view

### Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTN25050DFHTA	7	8	3,000

### Device marking

017

# ZXTN25050DFH

## Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	$V_{CBO}$	150	V
Collector-emitter voltage (forward blocking)	$V_{CEX}$	150	V
Collector-emitter voltage	$V_{CEO}$	50	V
Emitter-collector voltage (reverse blocking)	$V_{ECO}$	5	V
Emitter-base voltage	$V_{EBO}$	7	V
Continuous collector current <sup>(c)</sup>	$I_C$	4	A
Base current	$I_B$	1	A
Peak pulse current	$I_{CM}$	10	A
Power dissipation at $T_{amb} = 25^\circ\text{C}$ <sup>(a)</sup> Linear derating factor	$P_D$	0.73 5.84	W mW/°C
Power dissipation at $T_{amb} = 25^\circ\text{C}$ <sup>(b)</sup> Linear derating factor	$P_D$	1.05 8.4	W mW/°C
Power dissipation at $T_{amb} = 25^\circ\text{C}$ <sup>(c)</sup> Linear derating factor	$P_D$	1.25 9.6	W mW/°C
Power dissipation at $T_{amb} = 25^\circ\text{C}$ <sup>(d)</sup> Linear derating factor	$P_D$	1.81 14.5	W mW/°C
Operating and storage temperature range	$T_j, T_{stg}$	- 55 to 150	°C

## Thermal resistance

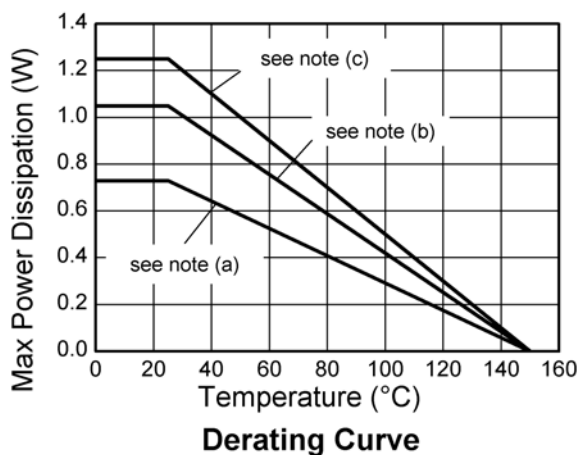
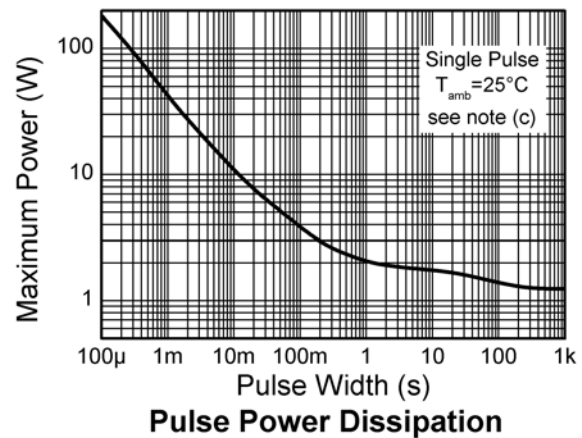
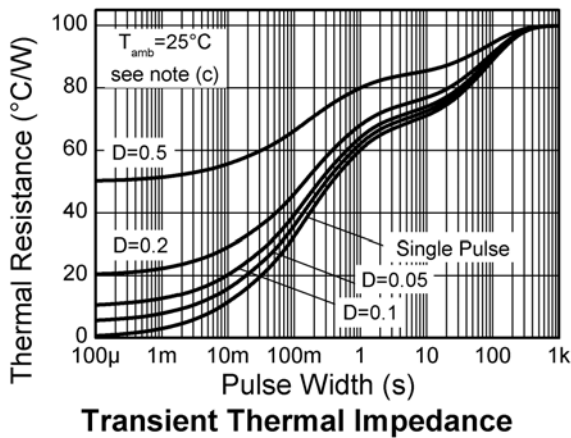
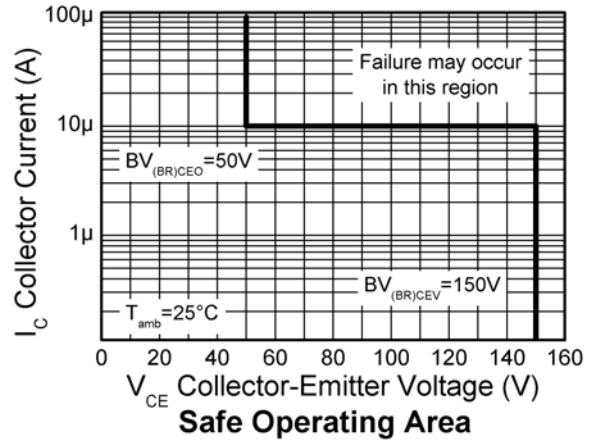
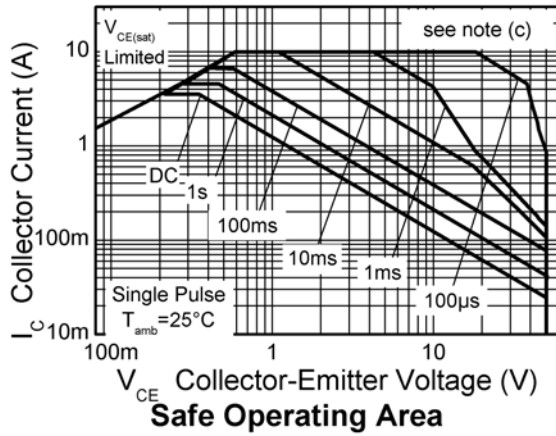
Parameter	Symbol	Limit	Unit
Junction to ambient <sup>(a)</sup>	$R_{\theta JA}$	171	°C/W
Junction to ambient <sup>(b)</sup>	$R_{\theta JA}$	119	°C/W
Junction to ambient <sup>(c)</sup>	$R_{\theta JA}$	100	°C/W
Junction to ambient <sup>(d)</sup>	$R_{\theta JA}$	69	°C/W

### NOTES:

- (a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- (b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.
- (c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.
- (d) As (c) above measured at  $t < 5\text{secs}$ .

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## Characteristics



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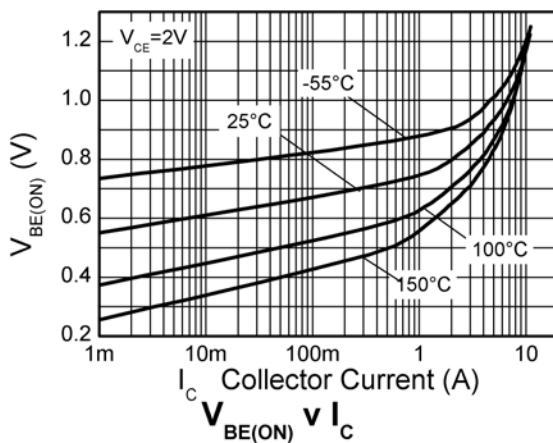
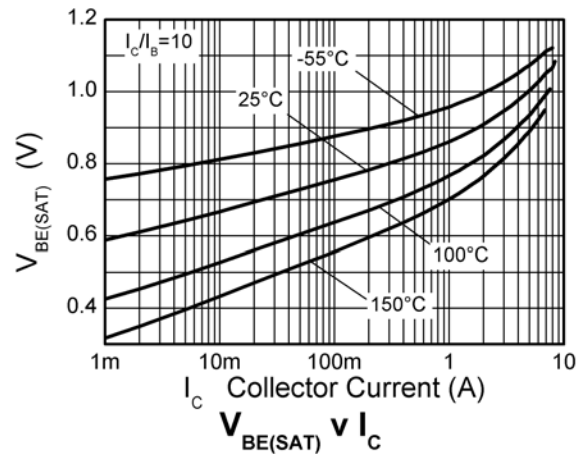
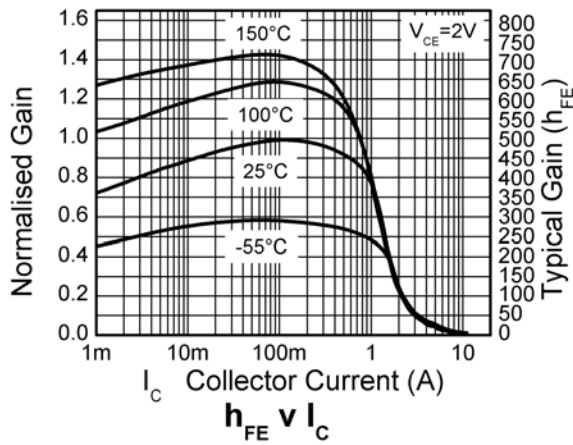
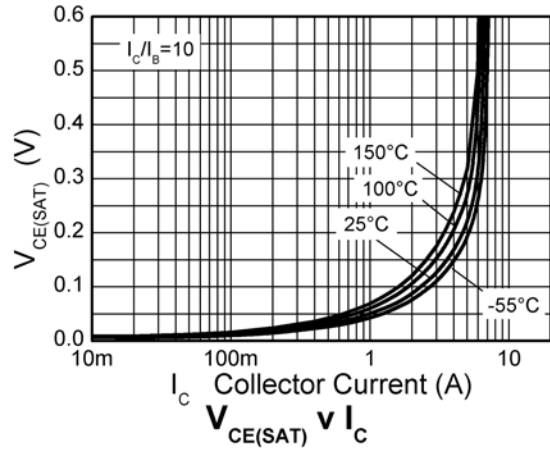
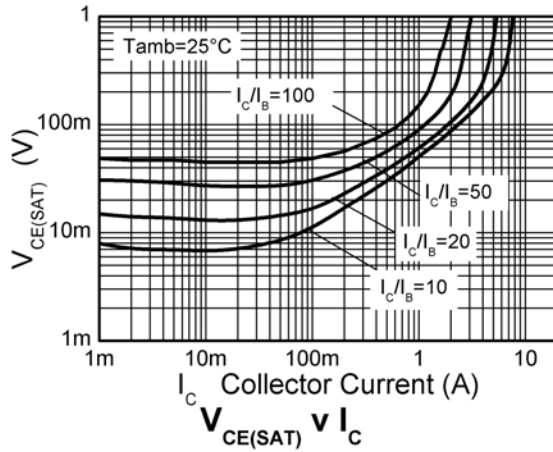
## Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	$BV_{CBO}$	150	180		V	$I_C = 100\mu\text{A}$
Collector-emitter breakdown voltage (forward blocking)	$BV_{CEX}$	150	180		V	$I_C = 100\mu\text{A}$ , $R_{BE} \leq 1\text{k}\Omega$ or $-1\text{V} < V_{BE} < 0.25\text{V}$
Collector-emitter breakdown voltage (base open)	$BV_{CEO}$	50	67		V	$I_C = 10\text{mA}^{(*)}$
Emitter-collector breakdown voltage (reverse blocking)	$BV_{ECX}$	5	8		V	$I_E = 100\mu\text{A}$ , $R_{BC} \leq 1\text{k}\Omega$ or $0.25\text{V} > V_{BC} > -0.25\text{V}$
Emitter-collector breakdown voltage (base open)	$BV_{ECO}$	5	7.4		V	$I_E = 100\mu\text{A}$ ,
Emitter-base breakdown voltage	$BV_{EBO}$	7	8.3		V	$I_E = 100\mu\text{A}$
Collector cut-off current	$I_{CBO}$		<1	50 20	nA $\mu\text{A}$	$V_{CB} = 150\text{V}$ $V_{CB} = 150\text{V}$ , $T_{amb} = 100^{\circ}\text{C}$
Collector-emitter cut-off current	$I_{CEX}$		-	100	nA	$V_{CE} = 150\text{V}$ ; $R_{BE} \leq 1\text{k}\Omega$ or $-1\text{V} < V_{BE} < 0.25\text{V}$
Emitter cut-off current	$I_{EBO}$		<1	50	nA	$V_{EB} = 5.6\text{V}$
Collector-emitter saturation voltage	$V_{CE(sat)}$		50 160 180 190 160	60 260 250 235 210	mV mV mV mV mV	$I_C = 1\text{A}$ , $I_B = 100\text{mA}^{(*)}$ $I_C = 1\text{A}$ , $I_B = 10\text{mA}^{(*)}$ $I_C = 2\text{A}$ , $I_B = 40\text{mA}^{(*)}$ $I_C = 3.5\text{A}$ , $I_B = 175\text{mA}^{(*)}$ $I_C = 4\text{A}$ , $I_B = 400\text{mA}^{(*)}$
Base-emitter saturation voltage	$V_{BE(sat)}$		970	1070	mV	$I_C = 4\text{A}$ , $I_B = 400\text{mA}^{(*)}$
Base-emitter turn-on voltage	$V_{BE(on)}$		870	970	mV	$I_C = 4\text{A}$ , $V_{CE} = 2\text{V}^{(*)}$
Static forward current transfer ratio	$h_{FE}$	300 240 20	450 410 40	900		$I_C = 10\text{mA}$ , $V_{CE} = 2\text{V}^{(*)}$ $I_C = 1\text{A}$ , $V_{CE} = 2\text{V}^{(*)}$ $I_C = 4\text{A}$ , $V_{CE} = 2\text{V}^{(*)}$
Transition frequency	$f_T$		200		MHz	$I_C = 50\text{mA}$ , $V_{CE} = 10\text{V}$ $f = 100\text{MHz}$
Output capacitance	$C_{OBO}$		12	20	pF	$V_{CB} = 10\text{V}$ , $f = 1\text{MHz}^{(*)}$
Delay time	$t_{(d)}$		65		ns	$V_{CC} = 10\text{V}$ . $I_C = 1\text{A}$ , $I_{B1} = I_{B2} = 10\text{mA}$ .
Rise time	$t_{(r)}$		111		ns	
Storage time	$t_{(s)}$		429		ns	
Fall time	$t_{(f)}$		140		ns	

### NOTES:

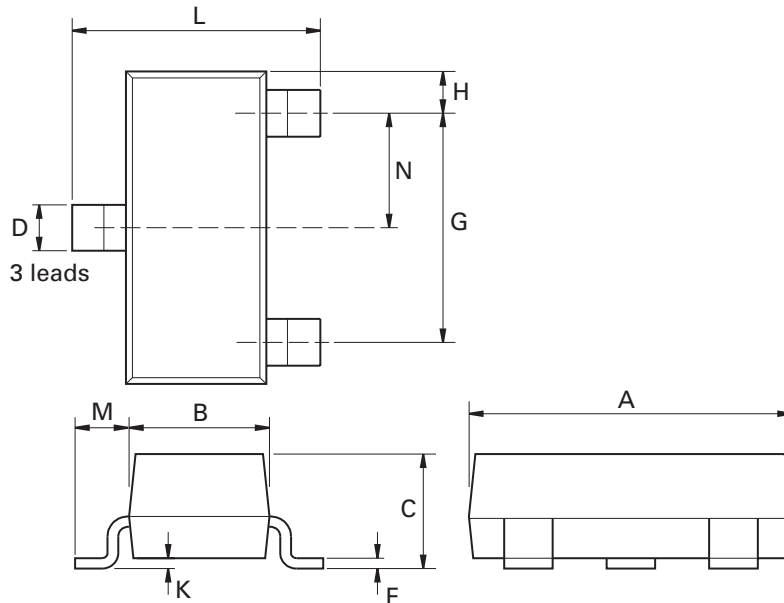
(\*) Measured under pulsed conditions. Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

## Typical characteristics



# ZXTN25050DFH

## Package outline - SOT23



Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Max.	Max.
A	2.67	3.05	0.105	0.120	H	0.33	0.51	0.013	0.020
B	1.20	1.40	0.047	0.055	K	0.01	0.10	0.0004	0.004
C	-	1.10	-	0.043	L	2.10	2.50	0.083	0.0985
D	0.37	0.53	0.015	0.021	M	0.45	0.64	0.018	0.025
F	0.085	0.15	0.0034	0.0059	N	0.95 NOM		0.0375 NOM	
G	1.90 NOM		0.075 NOM		-	-	-	-	-

**Note:** Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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